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## IN THE CLAIMS

1. (Currently Amended) An etching method comprising:  
providing a wafer having a dielectric layer and an electrode partially protruding from  
a top surface of the dielectric layer;  
etching the dielectric layer with a chemical solution; and  
prior to etching the dielectric layer, reducing the protruding portion of the electrode,  
wherein reducing the protruding portion includes recessing a top surface of the electrode at  
least 500 angstroms below the top surface of the dielectric layer.

2. (Original) The method of claim 1, wherein the protruding portion of the  
electrode is reduced sufficiently to prevent any bubbles included in the chemical solution  
from adhering to the electrode.

3-6. (Canceled)

7. (Original) The method of claim 1, wherein reducing the protruding portion  
comprises dry etching.

8. (Original) The method of claim 7, wherein drying etching uses an etchant  
selected from the group consisting of HB<sub>4</sub>, Cl<sub>2</sub>, CF<sub>4</sub>, C<sub>4</sub>F<sub>8</sub>, C<sub>5</sub>F<sub>8</sub>, SF<sub>6</sub>, O<sub>2</sub> and combinations  
thereof.

9. (Original) The method of claim 1, wherein reducing the protruding portion  
comprises wet etching.

10. (Original) The method of claim 9, wherein wet etching uses a polysilicon  
etchant.

11-41. (Canceled)